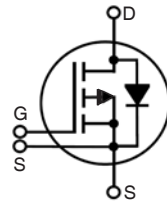


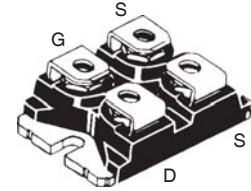
**TrenchP™  
Power MOSFET**
**IXTN120P20T**

P-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Rectifier



$$\begin{aligned} V_{DSS} &= -200V \\ I_{D25} &= -106A \\ R_{DS(on)} &\leq 30m\Omega \\ t_{rr} &\leq 300ns \end{aligned}$$

miniBLOC  
 E153432



G = Gate      D = Drain  
S = Source

Either Source Terminal S can be used as the Source Terminal or the Kelvin Source (Gate Return) Terminal.

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	- 200	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ , $R_{GS} = 1M\Omega$	- 200	V
$V_{GSS}$	Continuous	$\pm 15$	V
$V_{GSM}$	Transient	$\pm 25$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	-106	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , Pulse Width Limited by $T_{JM}$	- 400	A
$I_A$	$T_C = 25^\circ\text{C}$	-100	A
$E_{AS}$	$T_C = 25^\circ\text{C}$	3	J
dv/dt	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	830	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS, $t = 1$ minute	2500	V~
	$I_{ISOL} \leq 1\text{mA}$ , $t = 1\text{s}$	3000	V~
$M_d$	Mounting Torque for Base Plate	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g

**Features**

- International Standard Package
- Low Intrinsic Gate Resistance
- miniBLOC with Aluminum Nitride Isolation
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Rectifier
- Low  $R_{DS(ON)}$  and  $Q_G$

**Advantages**

- Easy to Mount
- Space Savings
- High Power Density

**Applications**

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = -250\mu\text{A}$	- 200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\mu\text{A}$	- 2.5		- 4.5 V
$I_{GSS}$	$V_{GS} = \pm 15V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			- 25 $\mu\text{A}$ - 300 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = -10V$ , $I_D = 60A$ , Note 1			30 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = -10\text{V}, I_D = -60\text{A}$ , Note 1	85	145	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = -25\text{V}, f = 1\text{MHz}$		73	nF
$C_{oss}$			2550	pF
$C_{rss}$			480	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = -10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = -60\text{A}$ $R_G = 1\Omega$ (External)		90	ns
$t_r$			85	ns
$t_{d(off)}$			200	ns
$t_f$			50	ns
$Q_{g(on)}$	$V_{GS} = -10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = -60\text{A}$		740	nC
$Q_{gs}$			220	nC
$Q_{gd}$			120	nC
$R_{thJC}$				0.15 $^\circ\text{C/W}$
$R_{thCS}$		0.05		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			-120 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			-480 A
$V_{SD}$	$I_F = -100\text{A}, V_{GS} = 0\text{V}$ , Note 1			-1.4 V
$t_{rr}$	$I_F = -60\text{A}, -di/dt = -100\text{A}/\mu\text{s}$ $V_R = -100\text{V}, V_{GS} = 0\text{V}$			300 ns
$Q_{RM}$			3.3	$\mu\text{C}$
$I_{RM}$			25.6	A

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### SOT-227B (IXTN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

### PRELIMINARY TECHNICAL INFORMATION

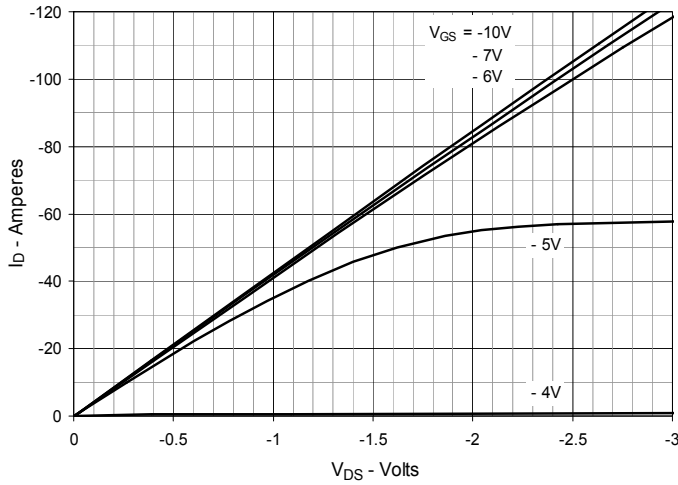
The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

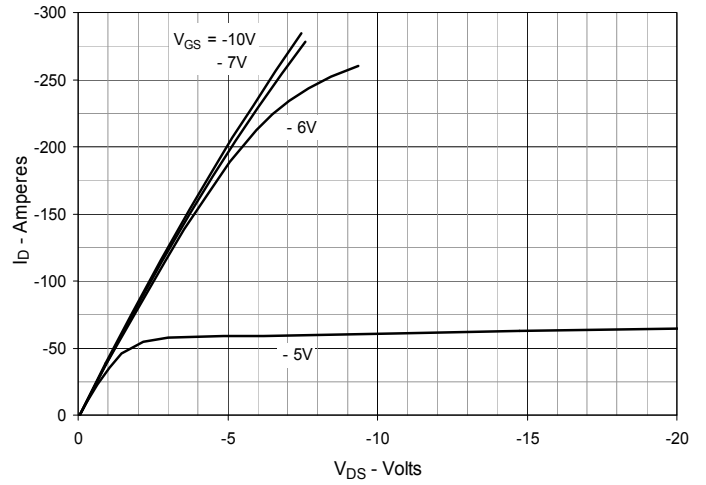
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

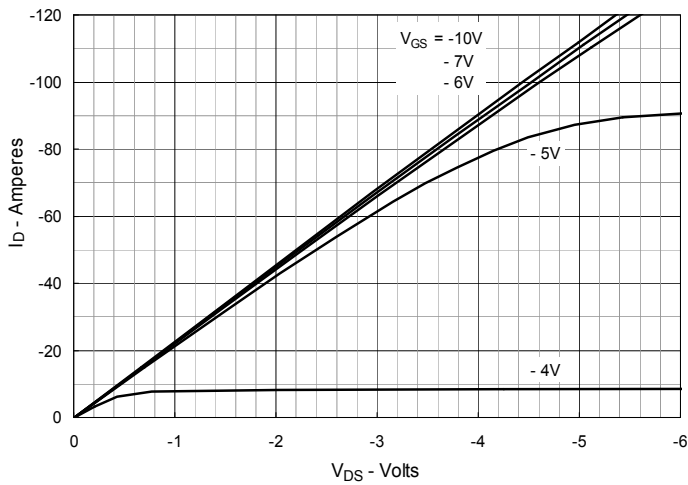
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



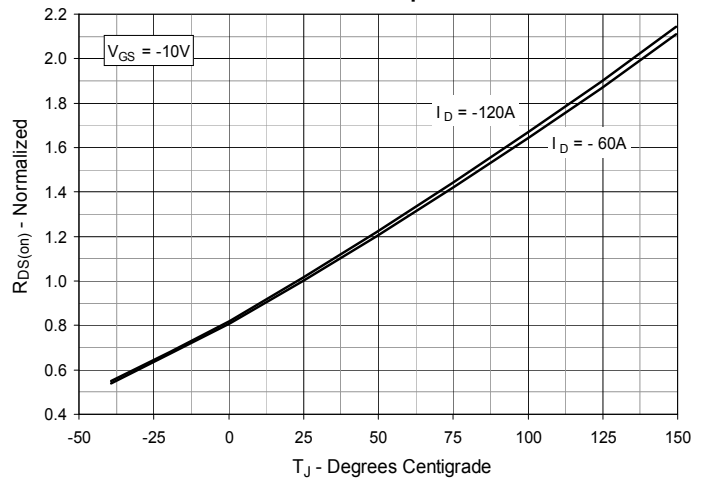
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



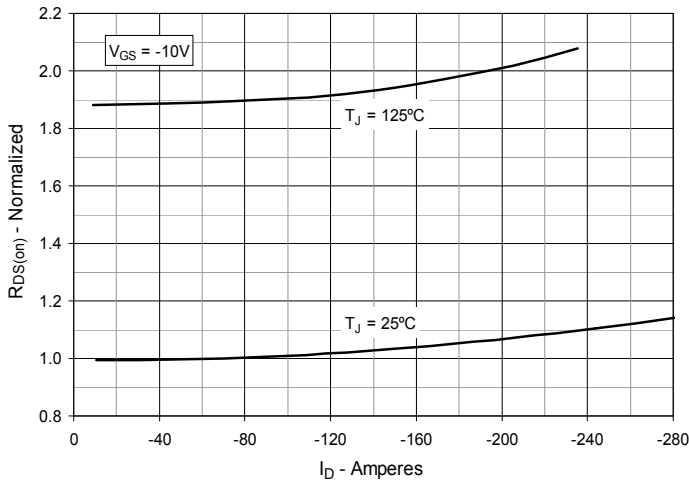
**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$**



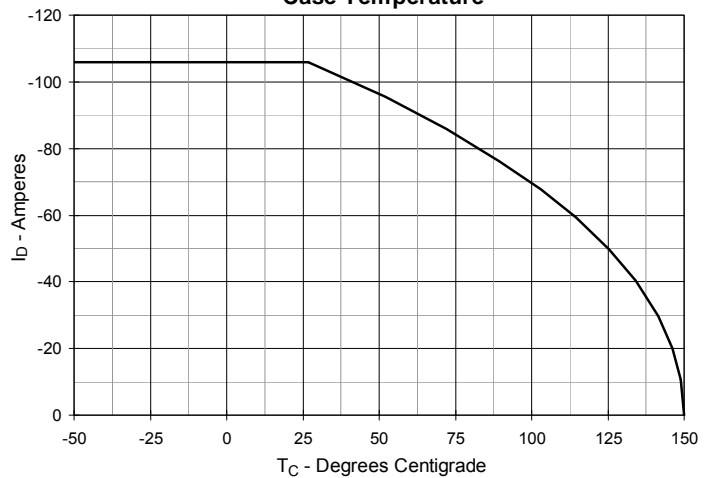
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = -60A$  Value vs. Junction Temperature**



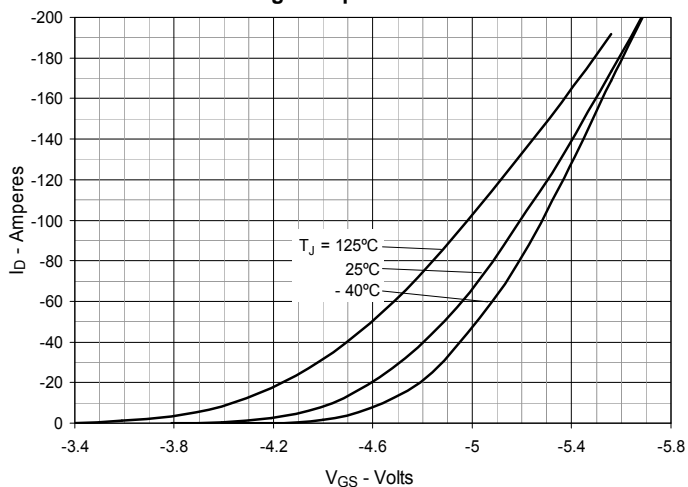
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = -60A$  Value vs. Drain Current**



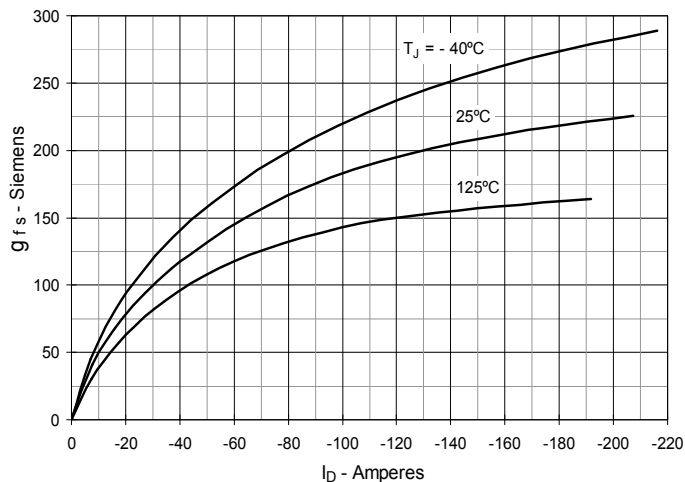
**Fig. 6. Maximum Drain Current vs. Case Temperature**



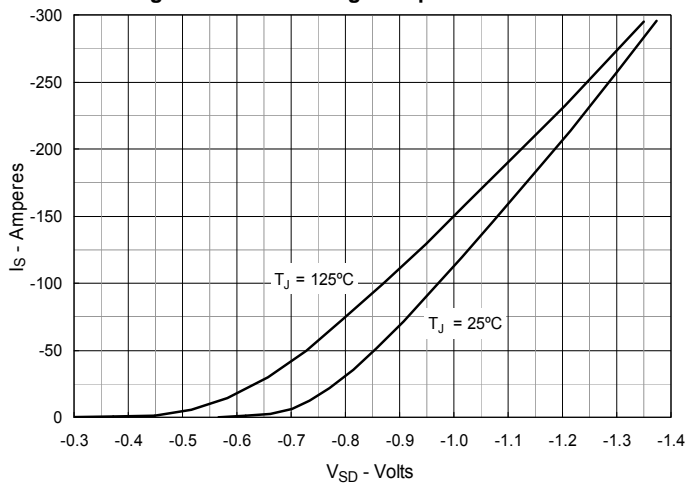
**Fig. 7. Input Admittance**



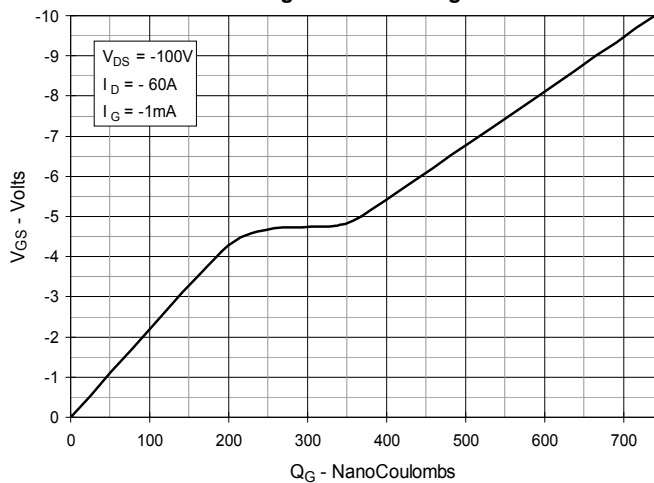
**Fig. 8. Transconductance**



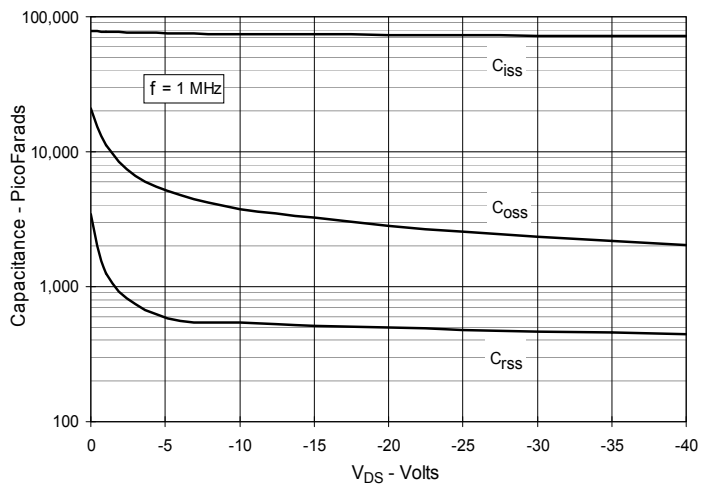
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



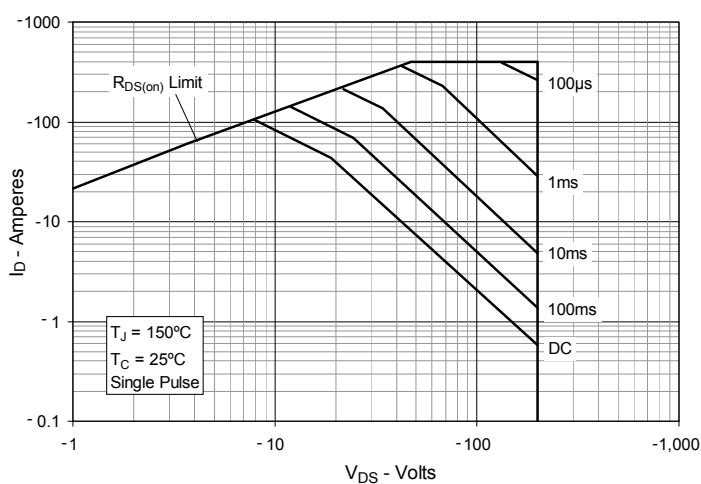
**Fig. 10. Gate Charge**



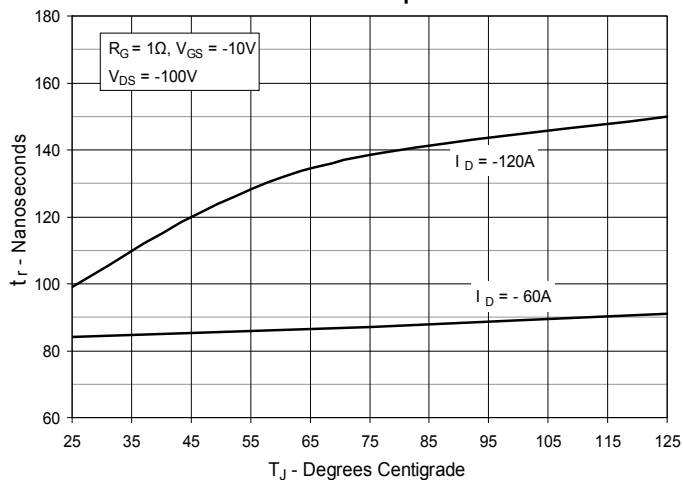
**Fig. 11. Capacitance**



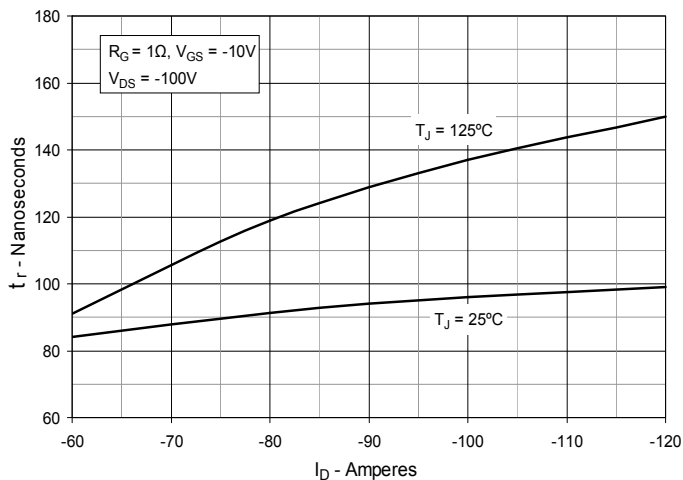
**Fig. 12. Forward-Bias Safe Operating Area**



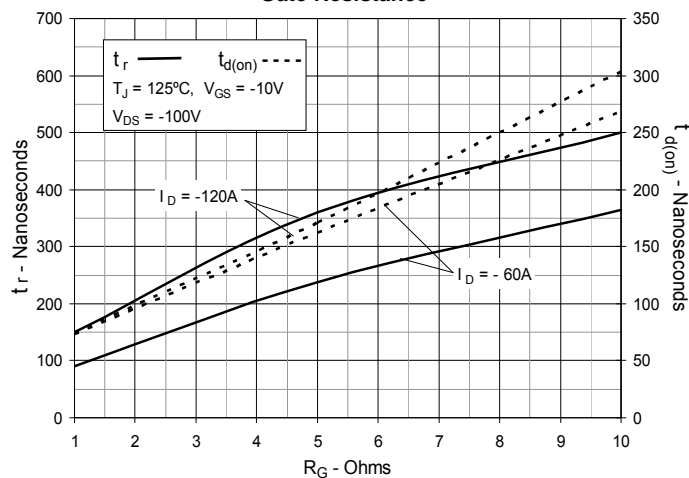
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



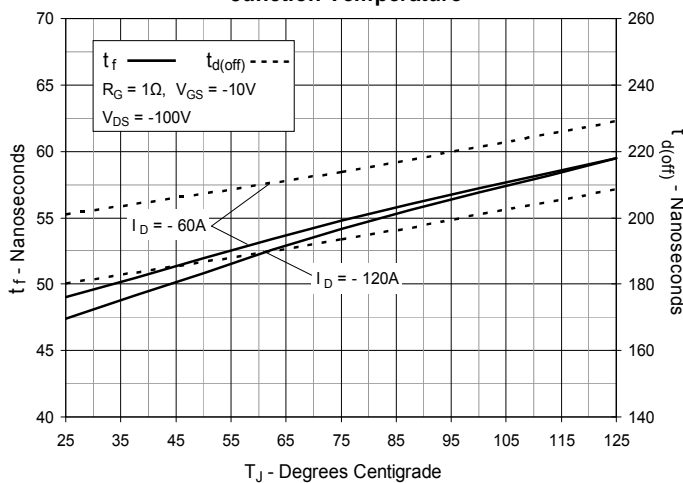
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



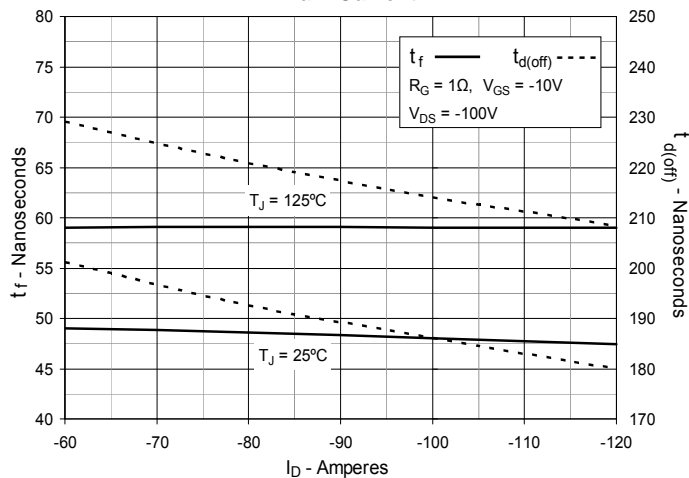
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

